

IN THE CLAIMS

Please amended the following claims:

30. (currently amended) A semiconductor device comprising:
a gate electrode formed on a gate dielectric formed on a substrate surface, the gate electrode having a first thickness;
a gate silicon germanium film formed on the gate electrode, the gate silicon germanium film having a second thickness;
a gate silicide layer formed on the gate silicon germanium film, the gate silicide layer having a third thickness;
a pair of sidewall spacers on opposite sides of the gate electrode, the sidewall spacers having a height of at least 200Å above the third thickness of the gate silicide layer [first height above the substrate surface, the first height greater than the sum of the first and second and third thicknesses];
a pair of source and drain regions formed on opposite sides of said gate electrode, said source and drain regions having a silicon germanium film formed beneath said substrate surface.

31. (original) The semiconductor device of claim 30, wherein the gate electrode is polysilicon.

32. (cancelled)

33. (previously amended) The semiconductor device of claim 30 further comprising:
a silicide layer formed on the silicon germanium film of said source and drain regions.

34. (previously amended) The semiconductor device of claim 33 further comprising:
an isolation region having a top surface positioned below the top surface of the silicon germanium film of said source and drain regions.

35. (original) The semiconductor device of claim 33 further comprising:
an isolation region having a top surface positioned below the silicide layer.

36. (currently amended) A semiconductor device comprising:
a silicon gate electrode formed on a gate dielectric formed on a substrate surface, the silicon gate electrode having a first thickness;
a gate silicon germanium film formed on the silicon gate electrode, the gate silicon germanium film having a second thickness;
a gate silicide layer formed on the gate silicon germanium film, the gate silicide layer having a third thickness;
a pair of sidewall spacers on opposite sides of the silicon gate electrode, the sidewall spacers having a height of at least 200Å above the third thickness of the gate silicide layer [first height above the substrate surface, the first height greater than the sum of the first and second and third thicknesses];
a pair of source/drain regions formed on opposite sides of the silicon gate electrode;
a source/drain silicon germanium film formed on the source/drain regions wherein said silicon germanium film is formed below said substrate surface; and
a source/drain silicide layer formed on the source/drain silicon germanium film.

37. (original) The semiconductor device of claim 36 wherein the silicon gate electrode is polysilicon.

38 - 43 (cancelled)
